

N-Channel Enhancement Mode Power MOSFET

Description

The RM90N40DF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

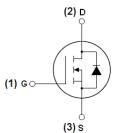
V_{DS} =40V,I_D =90A

 $R_{DS(ON)}$ <4 m Ω @ V_{GS}=10V

- $R_{DS(ON)} < 7 \text{ m}\Omega @ V_{GS} = 4.5 \text{V}$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram

s[1●	8]D
s[2	7]D
s[3	6 D
G[4	5]0

Marking and pin assignment



DFN5X6-8L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
90N40	RM90N40DF	DFN5X6-8L	-	-	-

Absolute Maximum Ratings (T_c=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	40	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	90	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	63.5	А
Pulsed Drain Current	I _{DM}	330	A
Maximum Power Dissipation	PD	65	W
Derating factor		0.43	W/°C
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	2.3	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)	ł		•			•
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.9	2.5	V
	P	V _{GS} =10V, I _D =20A	-	3.2	4.0	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =10A	-	5.5	7.0	
Forward Transconductance	G FS	V _{DS} =10V,I _D =20A	26	-	-	S
Dynamic Characteristics (Note4)	ł		•			•
Input Capacitance	C _{lss}		4600	5000	5400	PF
Output Capacitance	Coss	$V_{DS}=20V, V_{GS}=0V,$	826	898	970	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	324	351	380	PF
Switching Characteristics (Note 4)			•			•
Turn-on Delay Time	t _{d(on)}		-	15	-	nS
Turn-on Rise Time	tr	$V_{DD}=20V,I_{D}=20A,R_{L}=1\Omega$	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	52	-	nS
Turn-Off Fall Time	t _f		-	23	-	nS
Total Gate Charge	Qg	N/ 00// 00A	-	90		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=20V,I_{D}=20A,$	-	14		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	22		nC
Drain-Source Diode Characteristics	ł		•			•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	90	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 20A	-	42	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	45	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negli	gible (turr	n-on is do	ominated b	y LS+LD)

Notes:

 $\label{eq:linear} \textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$

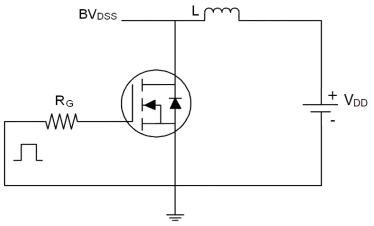
2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

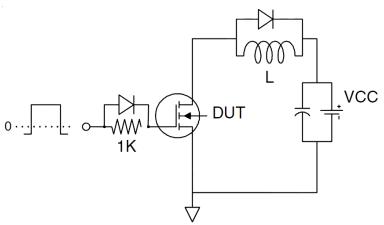
4. Guaranteed by design, not subject to production



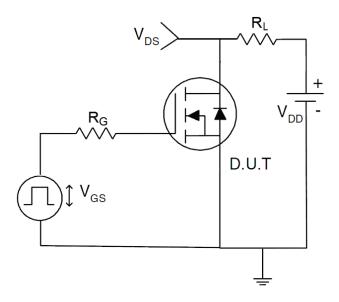
Test circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

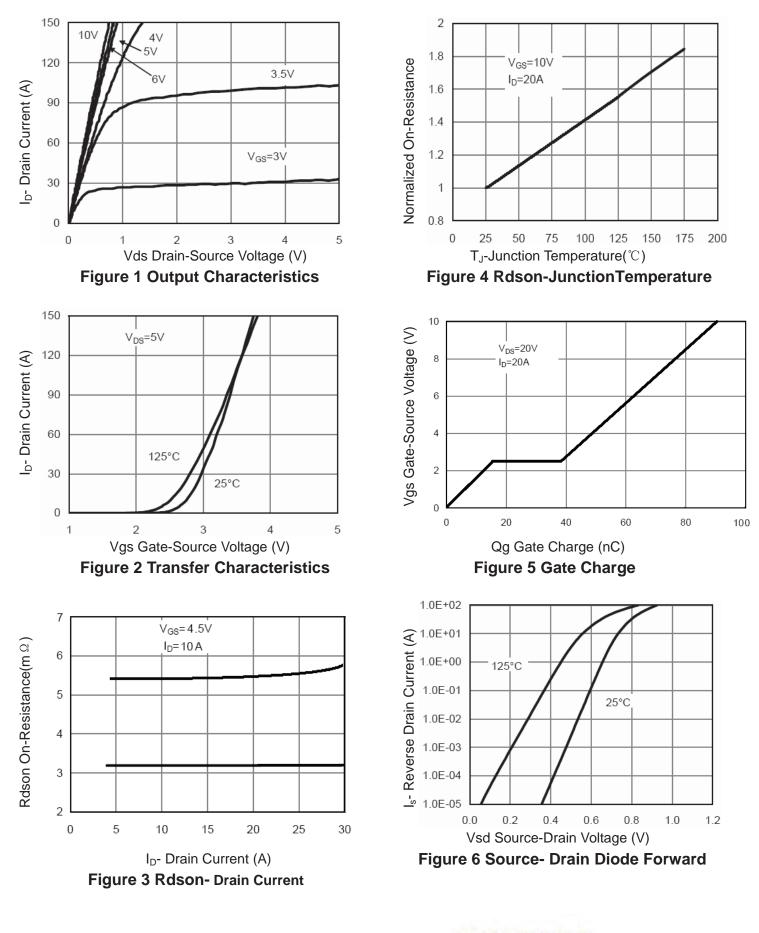


3) Switch Time Test Circuit



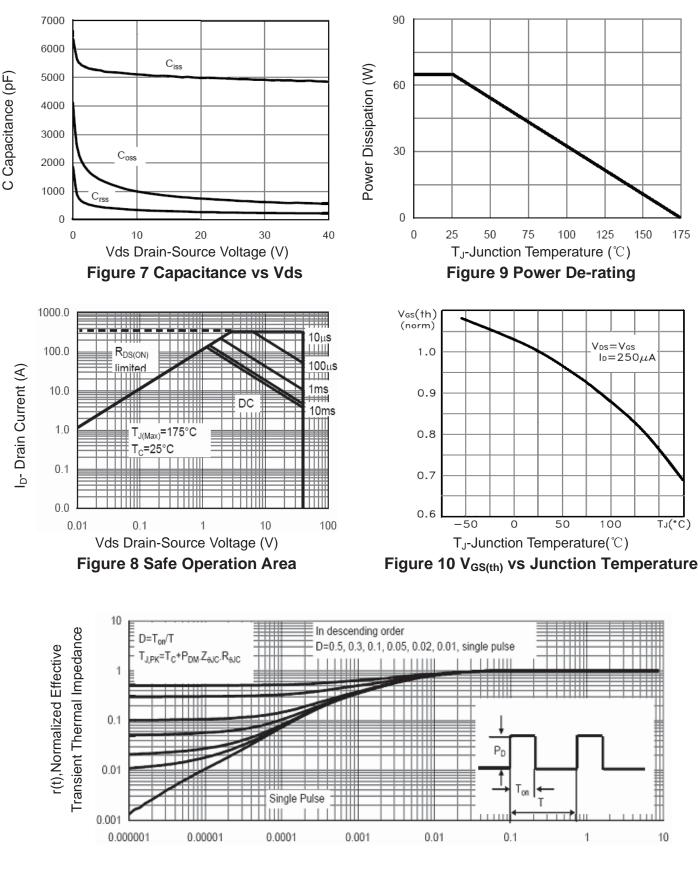


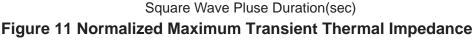
RATING AND CHARACTERISTICS CURVES (RM90N40DF)



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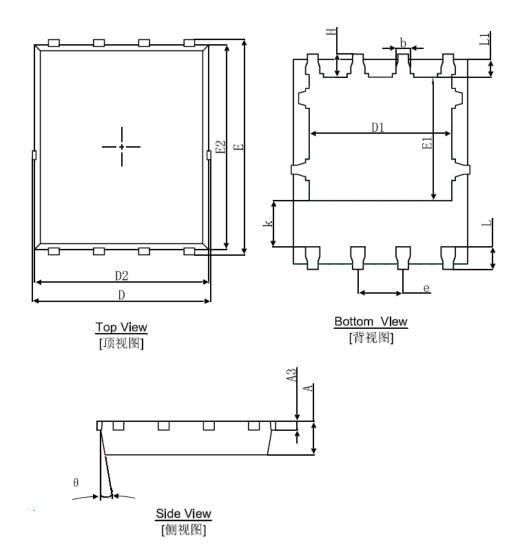
RATING AND CHARACTERISTICS CURVES (RM90N40DF)





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DFN5X6-8L Package Information



Cumula al	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.900	1.000	0.035	0.039	
A3	0.254	REF.	0.010	REF.	
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270	1.270TYP.		TYP.	
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	

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